

TrenchMOS™ transistor

Logic level FET

PHT8N06LT

GENERAL DESCRIPTION

N-channel enhancement mode logic level field-effect power transistor in a plastic envelope suitable for surface mounting. The device features very low on-state resistance and has integral zener diodes giving ESD protection. It is intended for use in DC-DC converters and general purpose switching applications.

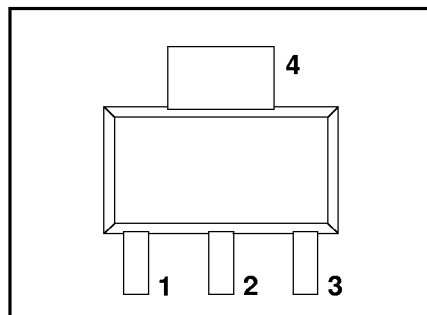
QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	UNIT
V_{DS}	Drain-source voltage	55	V
I_D	Drain current	7.5	A
P_{tot}	Total power dissipation	1.8	W
T_j	Junction temperature	150	°C
$R_{DS(ON)}$	Drain-source on-state resistance $V_{GS} = 5\text{ V}$	80	mΩ

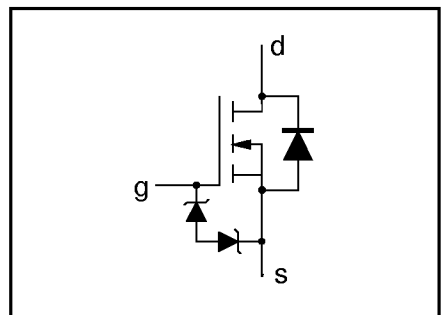
PINNING - SOT223

PIN	DESCRIPTION
1	gate
2	drain
3	source
4	drain (tab)

PIN CONFIGURATION



SYMBOL



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134)

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{DS}	Drain-source voltage	-	-	55	V
V_{DGR}	Drain-gate voltage	$R_{GS} = 20\text{ k}\Omega$	-	55	V
$\pm V_{GS}$	Gate-source voltage	-	-	13	V
I_D	Drain current (DC)	$T_{sp} = 25\text{ °C}$	-	7.5	A
I_D	Drain current (DC)	On PCB in Fig.2 $T_{amb} = 25\text{ °C}$	-	3.5	A
I_D	Drain current (DC)	$T_{amb} = 100\text{ °C}$	-	2.2	A
I_{DM}	Drain current (pulse peak value)	$T_{sp} = 25\text{ °C}$	-	40	A
P_{tot}	Total power dissipation	$T_{sp} = 25\text{ °C}$	-	8.3	W
P_{tot}	Total power dissipation	On PCB in Fig.2 $T_{amb} = 25\text{ °C}$	-	1.8	W
T_{stg}, T_j	Storage & operating temperature	-	- 55	150	°C

ESD LIMITING VALUE

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_C	Electrostatic discharge capacitor voltage	Human body model (100 pF, 1.5 kΩ)	-	2	kV

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THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
$R_{th\ j-sp}$	From junction to solder point	Mounted on any PCB	12	15	K/W
$R_{th\ j-amb}$	From junction to ambient	Mounted on PCB of Fig.17	-	70	K/W

STATIC CHARACTERISTICS

 $T_j = 25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$V_{(BR)DSS}$	Drain-source breakdown voltage	$V_{GS} = 0\text{ V}; I_D = 0.25\text{ mA}$ $T_j = -55^\circ\text{C}$	55 50	- -	- -	V V
$V_{GS(TO)}$	Gate threshold voltage	$V_{DS} = V_{GS}; I_D = 1\text{ mA}$ $T_j = 150^\circ\text{C}$ $T_j = -55^\circ\text{C}$	1.0 0.6 -	1.5 - -	2.0 - 2.3	V V V
I_{DSS}	Zero gate voltage drain current	$V_{DS} = 55\text{ V}; V_{GS} = 0\text{ V};$ $T_j = 150^\circ\text{C}$	- -	0.05 -	10 100	μA μA
I_{GSS}	Gate source leakage current	$V_{GS} = \pm 5\text{ V}$ $T_j = 150^\circ\text{C}$	- -	0.02 -	1 5	μA μA
$\pm V_{(BR)GSS}$	Gate source breakdown voltage	$I_G = \pm 1\text{ mA}$	10	-	-	V
$R_{DS(ON)}$	Drain-source on-state resistance	$V_{GS} = 5\text{ V}; I_D = 5\text{ A}$ $T_j = 150^\circ\text{C}$	- -	65 -	80 148	$\text{m}\Omega$ $\text{m}\Omega$

DYNAMIC CHARACTERISTICS

 $T_{mb} = 25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
g_{fs}	Forward transconductance	$V_{DS} = 25\text{ V}; I_D = 5\text{ A}; T_j = 25^\circ\text{C}$	4	-	-	S
$Q_{g(tot)}$	Total gate charge	$I_D = 7\text{ A}; V_{DD} = 44\text{ V}; V_{GS} = 5\text{ V}$	-	11.2	-	nC
Q_{gs}	Gate-source charge		-	2.2	-	nC
Q_{gd}	Gate-drain (Miller) charge		-	5	-	nC
C_{iss}	Input capacitance	$V_{GS} = 0\text{ V}; V_{DS} = 25\text{ V}; f = 1\text{ MHz}$	-	500	650	pF
C_{oss}	Output capacitance		-	110	135	pF
C_{rss}	Feedback capacitance		-	60	85	pF
$t_{d\ on}$	Turn-on delay time	$V_{DD} = 30\text{ V}; I_D = 7\text{ A};$	-	10	15	ns
t_r	Turn-on rise time	$V_{GS} = 5\text{ V}; R_G = 10\ \Omega;$	-	30	50	ns
$t_{d\ off}$	Turn-off delay time	$T_j = 25^\circ\text{C}$	-	30	45	ns
t_f	Turn-off fall time		-	30	40	ns

REVERSE DIODE LIMITING VALUES AND CHARACTERISTICS

 $T_j = -55$ to 175°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{DR}	Continuous reverse drain current	$T_{sp} = 25^\circ\text{C}$	-	-	7.5	A
I_{DRM}	Pulsed reverse drain current	$T_{sp} = 25^\circ\text{C}$	-	-	40	A
V_{SD}	Diode forward voltage	$I_F = 5\text{ A}; V_{GS} = 0\text{ V}$	-	0.85	1.1	V
t_{rr}	Reverse recovery time	$I_F = 5\text{ A}; -di_F/dt = 100\text{ A}/\mu\text{s};$	-	38	-	ns
Q_{rr}	Reverse recovery charge	$V_{GS} = -10\text{ V}; V_R = 30\text{ V}$	-	0.2	-	μC

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AVALANCHE LIMITING VALUE

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
W_{DSS}	Drain-source non-repetitive unclamped inductive turn-off energy	$I_D = 2.5\text{ A}$; $V_{DD} \leq 25\text{ V}$; $V_{GS} = 5\text{ V}$; $R_{GS} = 50\ \Omega$; $T_{sp} = 25\text{ °C}$	-	-	30	mJ

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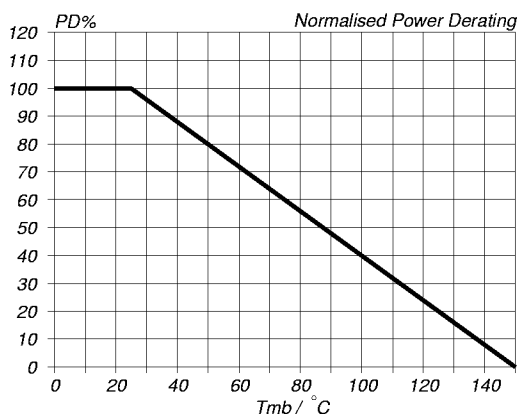


Fig.1. Normalised power dissipation.
 $PD\% = 100 \cdot P_D / P_{D\ 25^\circ\text{C}} = f(T_{sp})$

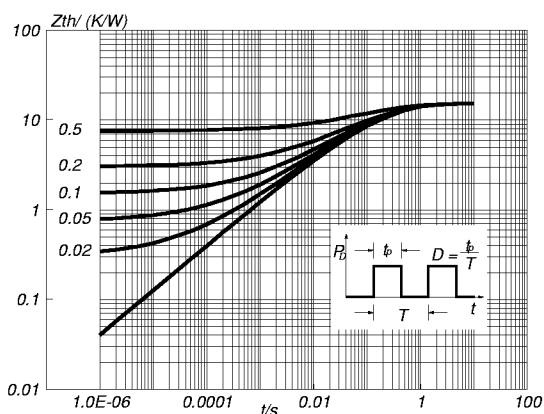


Fig.4. Transient thermal impedance.
 $Z_{th\ j-sp} = f(t)$; parameter $D = t_p / T$

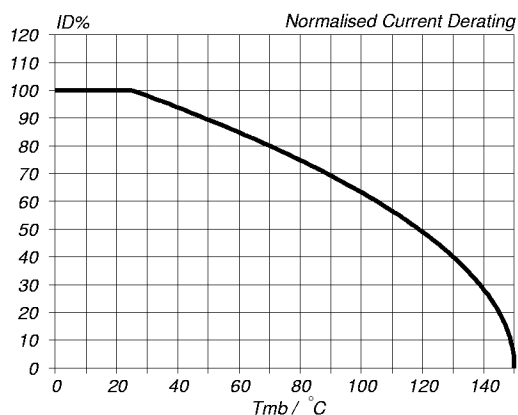


Fig.2. Normalised continuous drain current.
 $ID\% = 100 \cdot I_D / I_{D\ 25^\circ\text{C}} = f(T_{sp})$; conditions: $V_{GS} \geq 5\text{ V}$

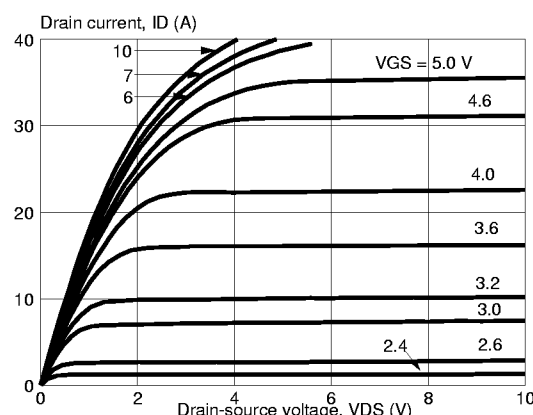


Fig.5. Typical output characteristics, $T_j = 25^\circ\text{C}$.
 $I_D = f(V_{DS})$; parameter V_{GS}

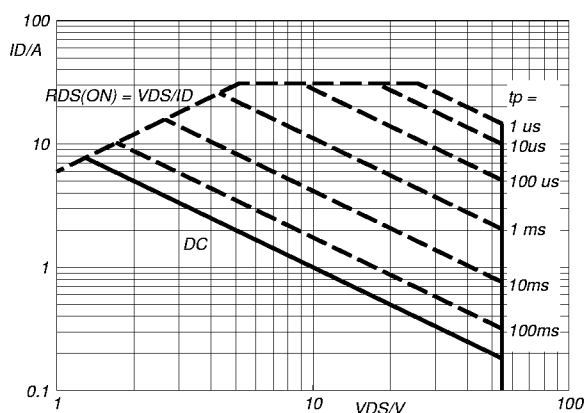


Fig.3. Safe operating area. $T_{sp} = 25^\circ\text{C}$
 I_D & $I_{DM} = f(V_{DS})$; I_{DM} single pulse; parameter t_p

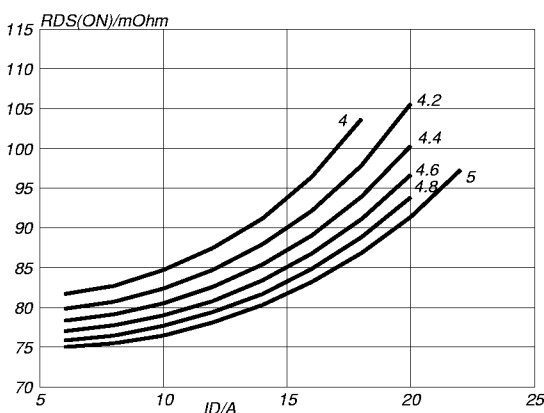
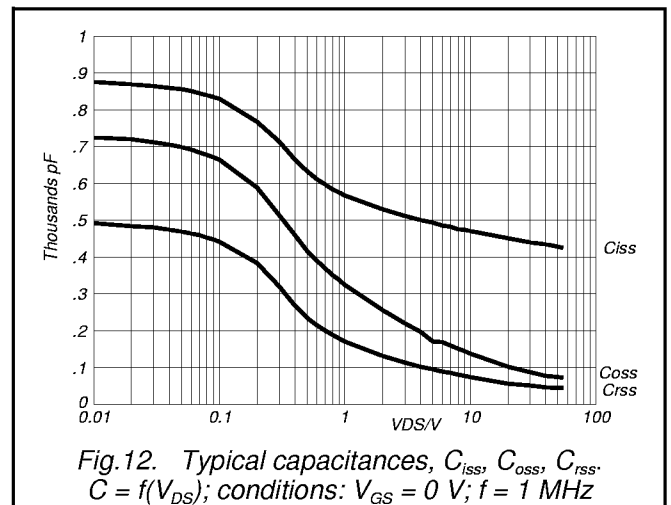
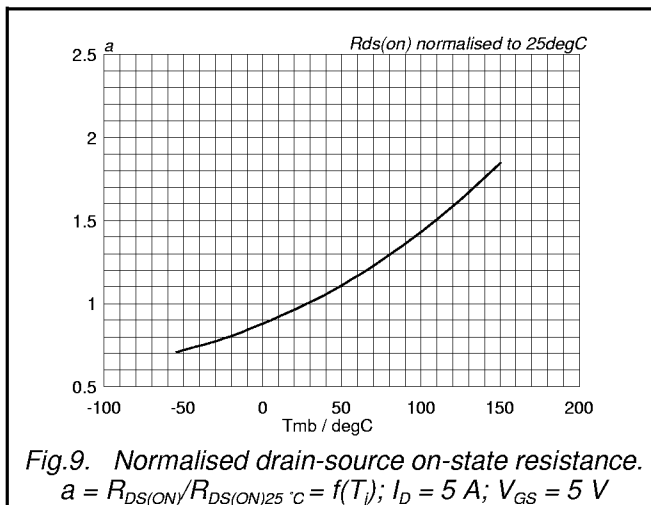
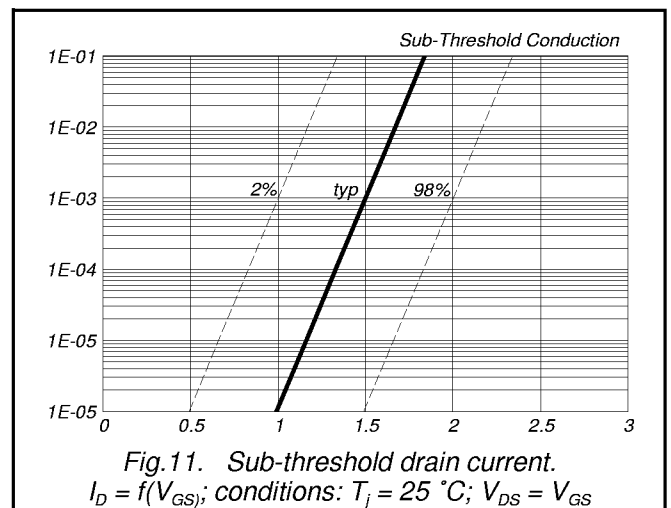
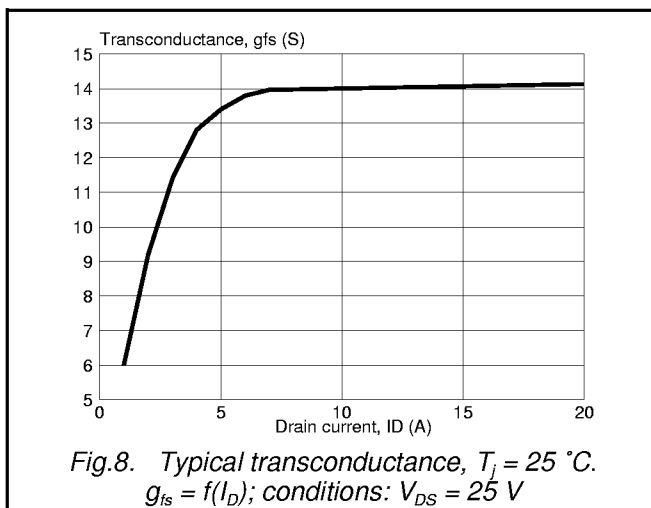
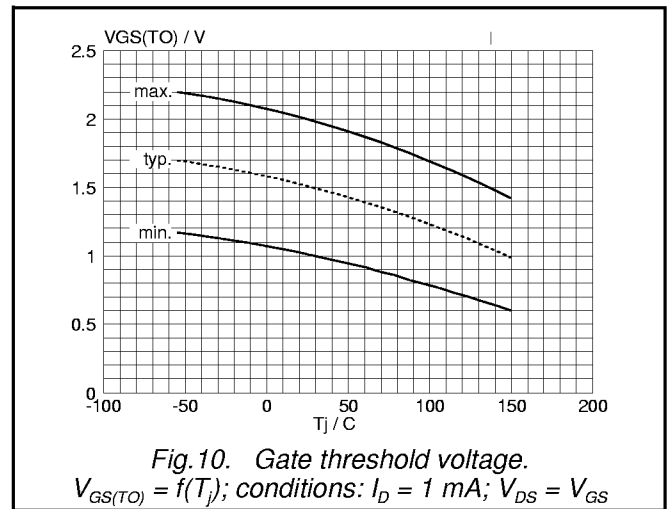
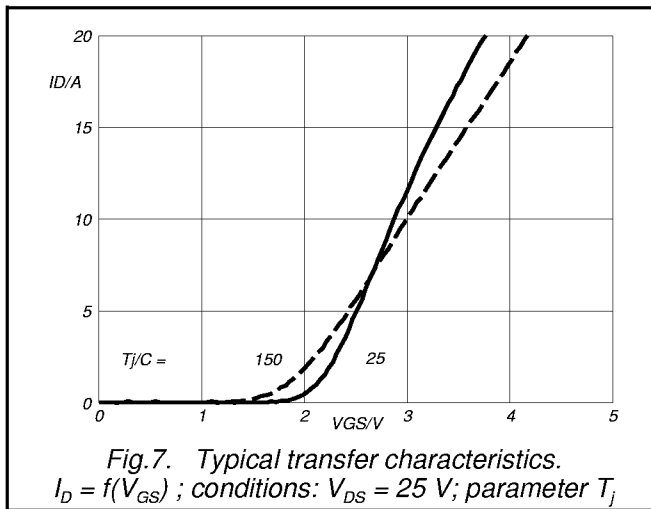


Fig.6. Typical on-state resistance, $T_j = 25^\circ\text{C}$.
 $R_{DS(ON)} = f(I_D)$; parameter V_{GS}

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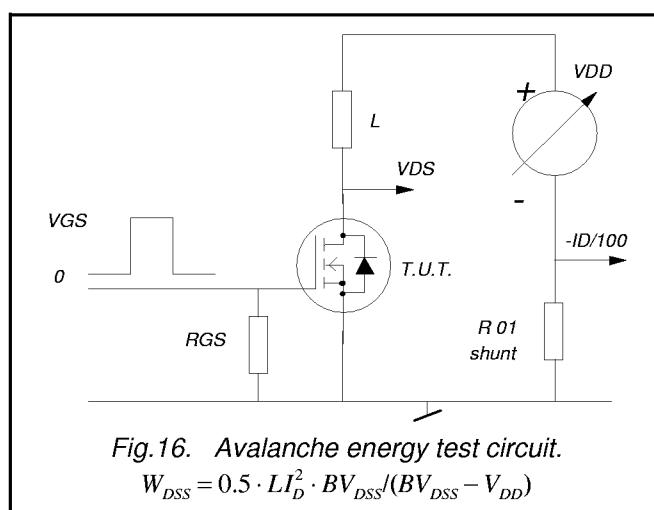
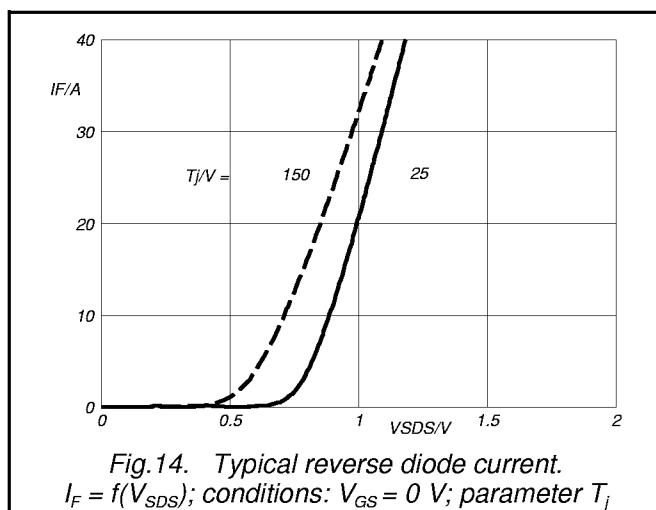
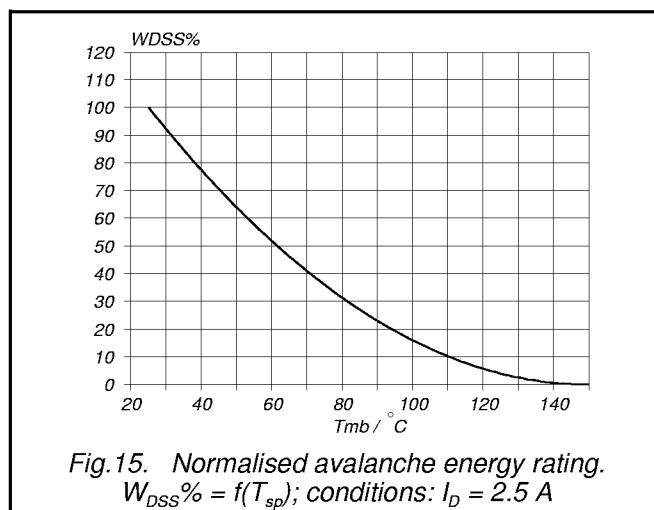
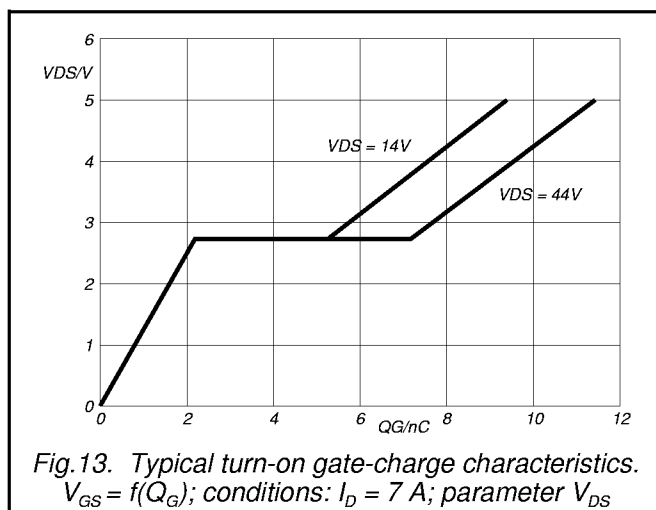
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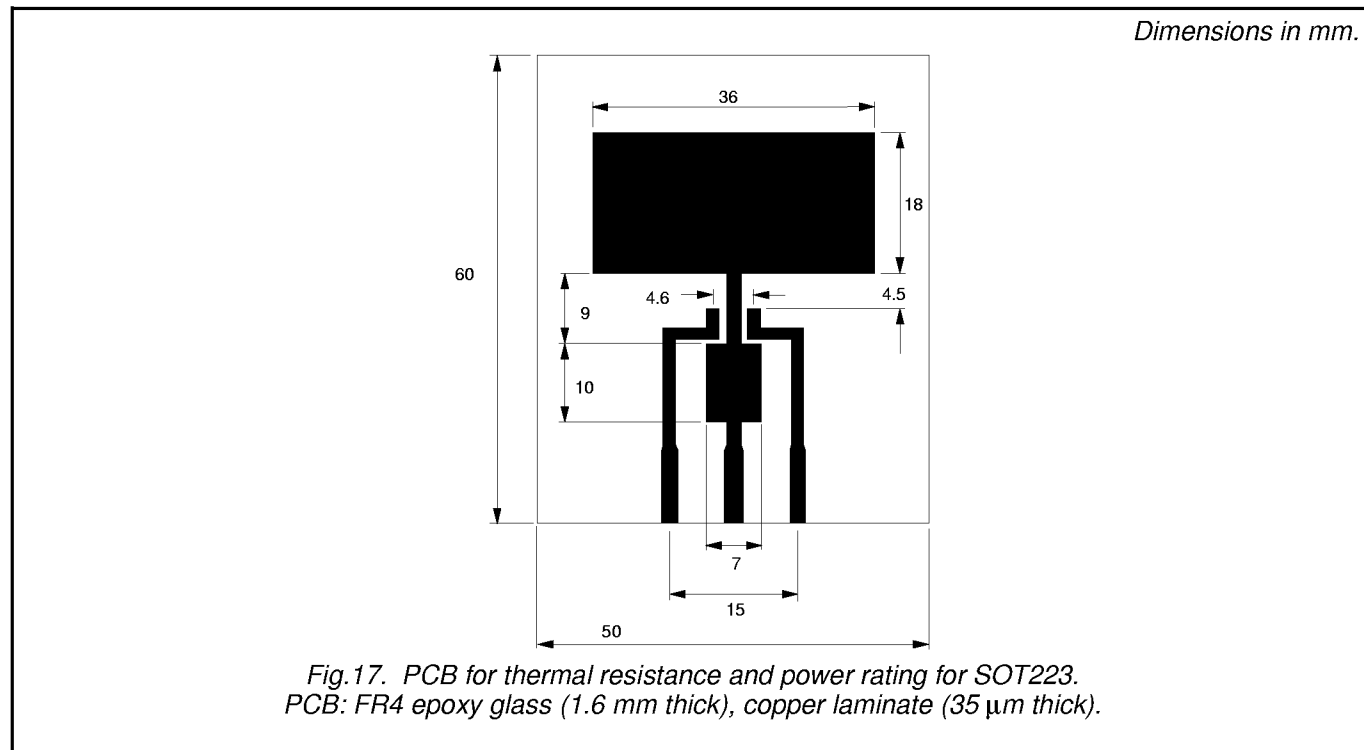


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PHT8N06LT



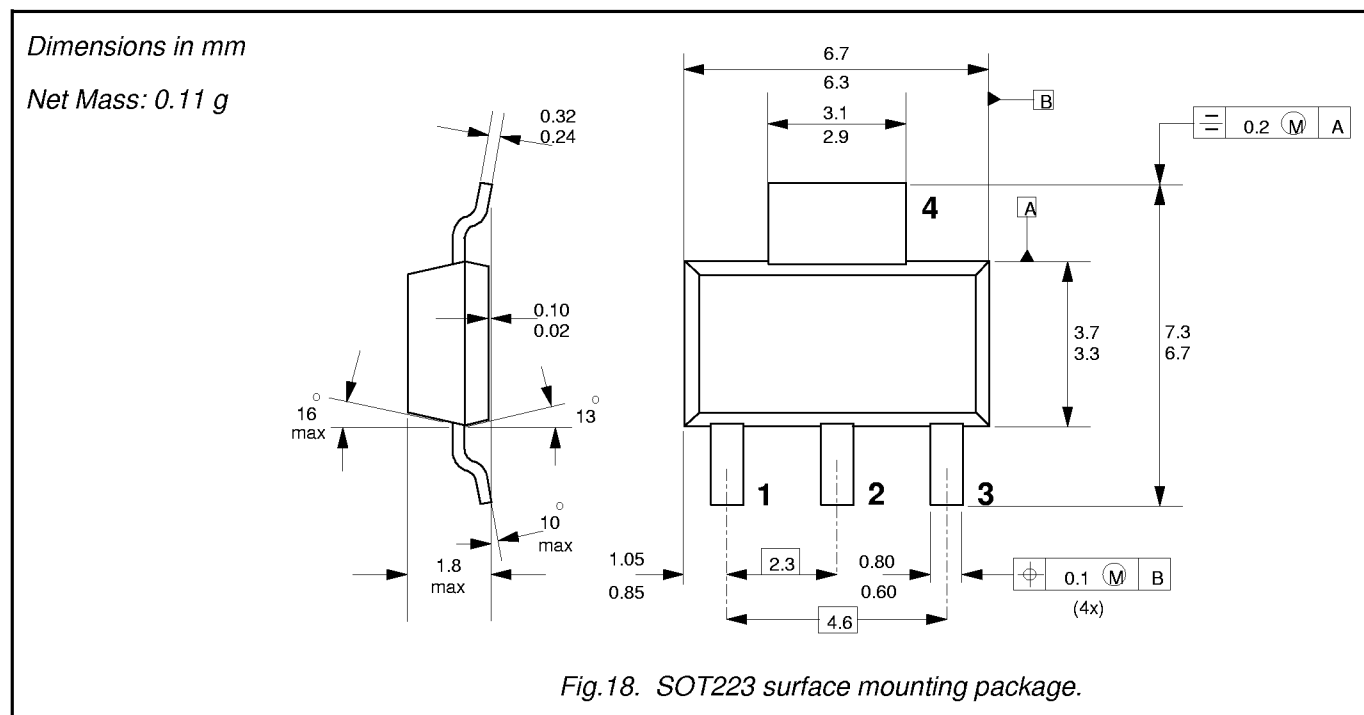
TrenchMOS™ transistor
Logic level FET**PHT8N06LT****PRINTED CIRCUIT BOARD**

TrenchMOS™ transistor

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PHT8N06LT

MECHANICAL DATA



Notes

1. Observe the general handling precautions for electrostatic-discharge sensitive devices (ESDs) to prevent damage to MOS gate oxide.
2. Refer to surface mounting instructions for SOT223 envelope.
3. Epoxy meets UL94 V0 at 1/8".